

AMENDMENTS TO THE CLAIMS

Claim 1 (currently amended): A semiconductor device having a surface, comprising:

~~characterized by having boron, carbon and nitrogen as main components, and a coating to which sulfur has been added serves as surface protection and covers at least part of a surface~~

a coating disposed on said semiconductor device surface to cover at least a portion thereof, said coating including boron, carbon, nitrogen and sulfur.

Claim 2 (currently amended): The semiconductor device of Claim 1, ~~characterized in that~~ wherein a carbon composition ratio (atomic ratio) of the coating is at least 0.1.

Claim 3 (currently amended): The semiconductor device of ~~one of~~ Claim 1 and Claim 2, ~~characterized in that~~ oxygen is included in the coating wherein said coating includes oxygen.

Claim 4 (currently amended): The semiconductor device of ~~any one of Claims 1 to 3~~ Claim 1, further includes ~~characterized by having~~ a multi-layer structure with a heterogeneous film attached to the coating.

Claim 5 (currently amended): The semiconductor device of ~~any one of Claims 1 to 4~~ Claim 4, ~~characterized in that~~ the

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wherein said heterogeneous film contains an amount of structural elements different ~~to~~ than the coating.

Claim 6 (currently amended): The semiconductor device of any one of Claims 1 to 4 Claim 4, characterized in that the wherein said heterogeneous film is a film with main components identical to the coating, without sulfur being added thereto.

Claim 7 (currently amended): The semiconductor device of any one of Claims 1 to 4 Claim 4, characterized in that the wherein said heterogeneous film is a film with silicon as a main component.

Claim 8 (currently amended): The semiconductor device of any one of Claims 1 to 7 Claim 1, characterized by having further includes a III-V compound semiconductor.

Claim 9 (currently amended): The semiconductor device of any one of Claims 1 to 8 Claim 8, characterized in that the wherein said semiconductor is a field effect transistor.

Claim 10 (currently amended): The semiconductor device of any one of Claims 1 to 9 Claim 8, characterized in that the wherein said semiconductor is a bipolar transistor.

Claim 11 (currently amended): The semiconductor device of any one of Claims 1 to 8 Claim 8, characterized in that the wherein said semiconductor is a diode.

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Claim 12 (currently amended): A semiconductor device fabrication method, ~~characterized by said method comprising the steps of:~~

disposing a film formation substrate in a plasma atmosphere containing nitrogen[,]; and

supplying boron atoms, carbon atoms and sulfur atoms to the film formation substrate[,] and ~~forming to thereby form a boron carbon nitride film to which sulfur has been added having sulfur as an additive thereto.~~

Claim 13 (currently amended): A semiconductor device fabrication method, ~~characterized by said method comprising the steps of:~~

disposing a film formation substrate facing a boron nitride sputter portion[,]; and

supplying carbon atoms and sulfur atoms to the film formation substrate[,] and ~~forming to thereby form a boron carbon nitride film to which sulfur has been added having sulfur as an additive thereto.~~

Claim 14 (currently amended): A semiconductor device fabrication method, ~~characterized by said method comprising the steps of:~~

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disposing a film formation substrate facing a boron nitride  
5 and carbon sputter portion[,]; and

supplying sulfur atoms to the film formation substrate[,]  
and ~~forming to thereby form~~ a boron carbon nitride film ~~to which~~  
~~sulfur has been added~~ having sulfur as an additive thereto.

Claim 15 (currently amended): A semiconductor device  
fabrication method, ~~characterized by~~ said method comprising the  
steps of:

disposing a film formation substrate facing a boron nitride  
5 laser abrasion[,]; and

supplying plasma containing carbon atoms and sulfur atoms  
to the film formation substrate[,]  
~~and forming to thereby form~~  
a boron carbon nitride film ~~to which sulfur has been added~~  
having sulfur as an additive thereto.

Claim 16 (currently amended): A semiconductor device  
fabrication method, ~~characterized by~~ said method comprising the  
steps of:

disposing a film formation substrate facing a boron nitride  
5 and carbon laser abrasion[,]; and

supplying plasma containing sulfur atoms to the film  
formation substrate[,]  
~~and forming to thereby form~~ a boron

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~~carbon nitride film to which sulfur has been added~~ having sulfur as an additive thereto.

Claim 17 (original): The semiconductor device fabrication method of any one of Claims 12 to 16, characterized in that the semiconductor is a field effect transistor.

Claim 18 (original): The semiconductor device fabrication method of any one of Claims 12 to 16, characterized in that the semiconductor is a bipolar transistor.

Claim 19 (original): The semiconductor device fabrication method of any one of Claims 12 to 16, characterized in that the semiconductor is a diode.

Claim 20 (currently amended): A communication system device, ~~characterized by having the semiconductor device of any one of~~ Claims 1 to 11 comprising:

a semiconductor device having a surface; and  
a coating disposed on said semiconductor device surface to  
cover at least a portion thereof, said coating including boron,  
carbon, nitrogen and sulfur.